

<b>FORM PTO-1449</b>				Atty. Docket No. <del>XA-9801A</del> <b>XA-9801B</b>		Appl. No. <b>10/673,217</b>	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b>				Applicant <b>Atsushi KUROKAWA et al.</b>			
				Filing Date <del>HEREWITH</del> <b>9-30-03</b>		Group <b>2829</b>	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
CC	AA	5,077,231	12/31/91	Plumton et al.	438	170	
CC	AB	5,166,083	11/24/92	Bayraktaroglu	438	170	
CC	AC	5,268,315	12/07/93	Prasad et al.	438	314	
CC	AD	5,324,671	06/28/94	Bayraktaroglu	438	317	
CC	AE	5,672,522	09/30/97	Streit et al.	438	312	
	AF						
	AG						
	AH						
	AI						
<b>FOREIGN PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
CC	AJ	2001-210723	08/03/01	Japan			Abstract
	AK						
	AL						
	AM						
	AN						
	AO						
<b>OTHER</b> (including author, title, date, pertinent pages, etc.)							
CC	AP	Chen et al., "High-Speed InGaP/GaAs HBT's Using a Simple Collector Undercut Technique to Reduce Base-Collector Capacitance," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 7, July 1997, pp. 355-357.					
CC	AQ	Ahmari et al., "InGaP/CaAs Heterojunction Bipolar Transistor Grown on a Semi-Insulating InGaP Buffer Layer," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 11, November 1997, pp. 559-561.					
	AR						
Examiner <b>Chandra Chaudhari</b>				Date Considered <b>2-05</b>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							